

**40V, 189A, 1.8mΩ N-channel Power SGT MOSFET**
**JMSH0402MGQ**
**Features**

- Ultra-low ON-resistance,  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100%  $\Delta V_{ds}$  Tested
- Halogen-free; RoHS-compliant
- AEC-Q101 Qualified

**Applications**

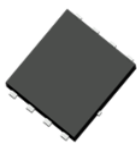
- Load Switch
- PWM Application
- General Automotive Application

**Product Summary**

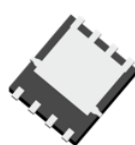
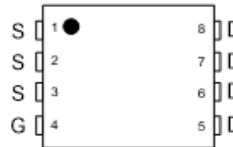
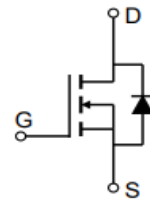
Parameters	Value	Unit
$V_{DSS}$	40	V
$V_{GS(th)}_{Typ}$	2.7	V
$I_D(@V_{GS}=10V)$	189	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	1.8	mΩ



Top View



Bottom View


**PDFN5X6-8L**

**Pin Assignment**

**Schematic Diagram**
**Ordering Information**

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0402MGQ-13	SH0402MQ	1	Tape&Reel	PDFN5x6-8L	5000	50000

**Absolute Maximum Ratings (@  $T_C = 25^\circ\text{C}$  unless otherwise specified)**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	40	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	189
		$T_C = 100^\circ\text{C}$	134
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	459	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	157
		$T_C = 100^\circ\text{C}$	78
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 175	$^\circ\text{C}$

**Thermal Characteristics**

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	42	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.0	

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$ , $V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	1.9	2.7	3.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10\text{V}$ , $I_D = 20\text{A}$	-	1.8	2.4	m $\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	0.9	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ , $V_{DS} = 20\text{V}$ , $f = 1\text{MHz}$	2589	3625	4893	pF
$C_{oss}$	Output Capacitance		1413	1979	2671	pF
$C_{riss}$	Reverse Transfer Capacitance		113	158	213	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0$ to $10\text{V}$ $V_{DS} = 20\text{V}$ , $I_D = 20\text{A}$	42	59	80	nC
$Q_{gs}$	Gate Source Charge		11	15	21	nC
$Q_{gd}$	Gate Drain ("Miller") Charge		12	16	22	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$ , $V_{DD} = 20\text{V}$ $I_D = 20\text{A}$ , $R_{GEN} = 3\Omega$	-	16	-	ns
$t_r$	Turn-On Rise Time		-	29	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	35	-	ns
$t_f$	Turn-Off Fall Time		-	13	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	189	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	756	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = 20\text{A}$	-		1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$	37	52	70	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	66	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 20\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 17.5\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a  $1\text{inch}^2$  pad of 2oz copper FR4 PCB.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .



## Typical Performance Characteristics

Figure 1: Power De-rating

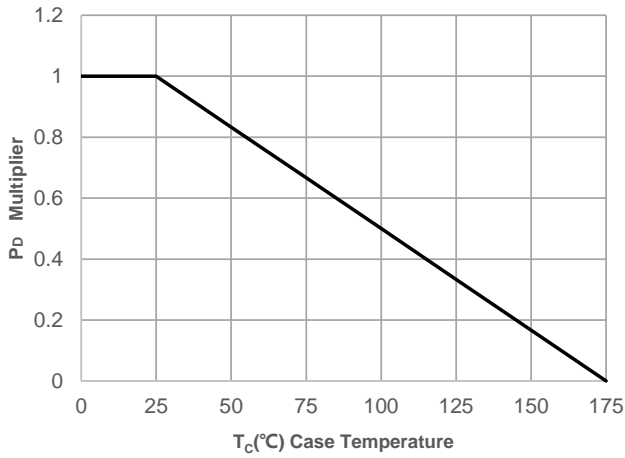


Figure 2: Current De-rating

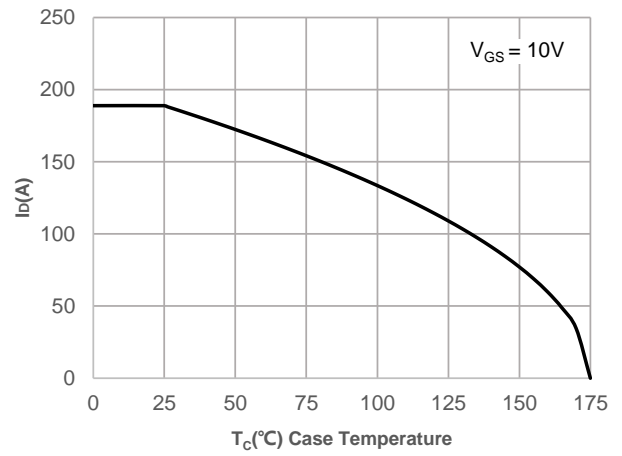


Figure 3: Normalized Maximum Transient Thermal Impedance

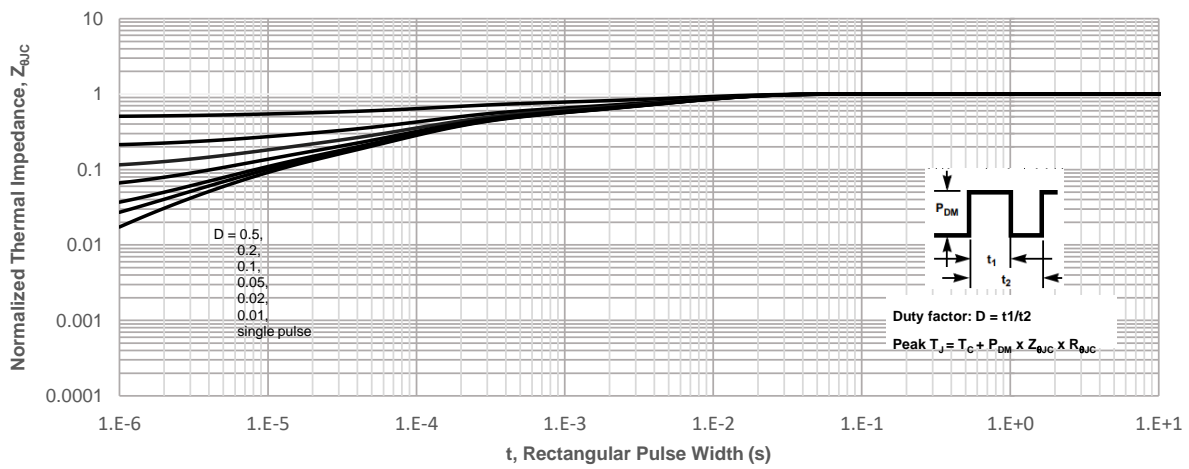
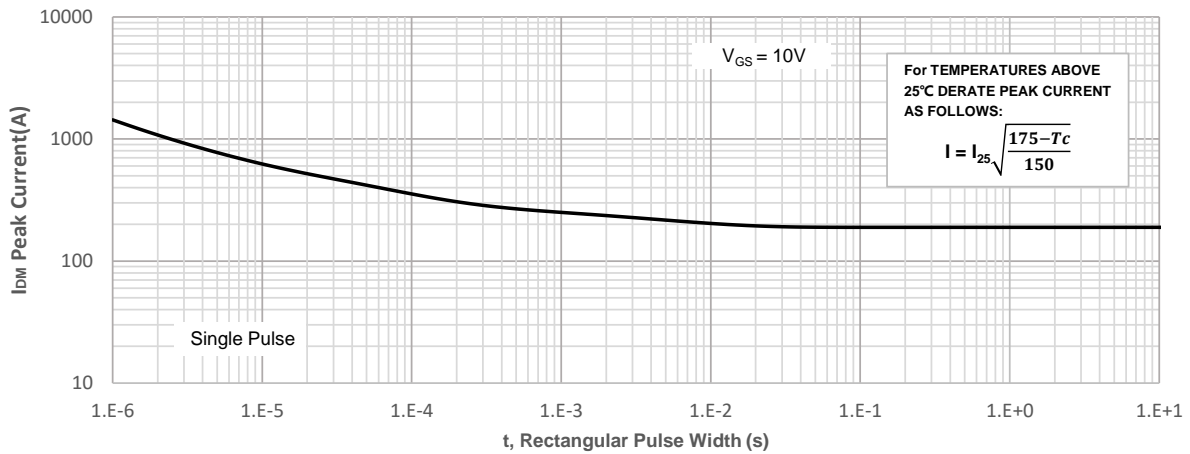


Figure 4: Peak Current Capacity



## Typical Performance Characteristics

Figure 5: Output Characteristics

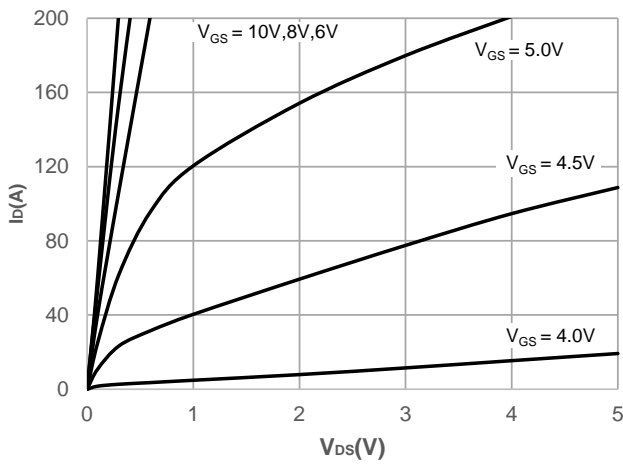


Figure 6: Typical Transfer Characteristics

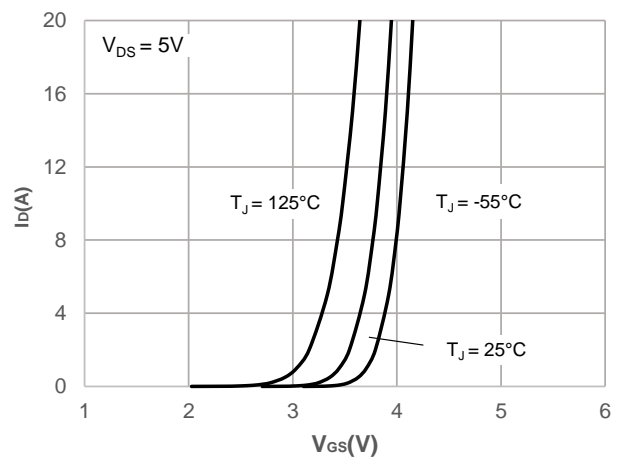


Figure 7: On-resistance vs. Drain Current

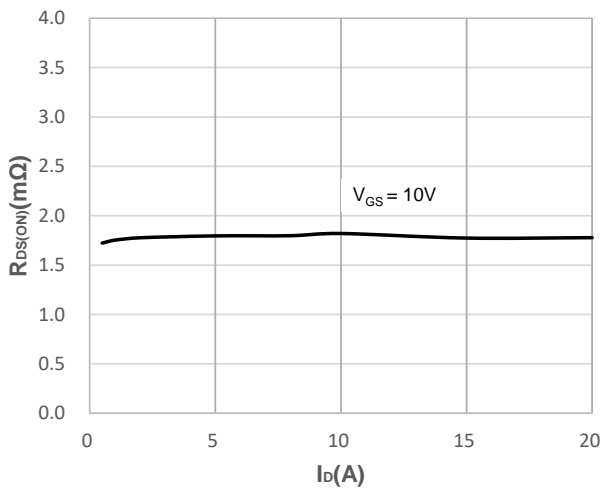


Figure 8: Body Diode Characteristics

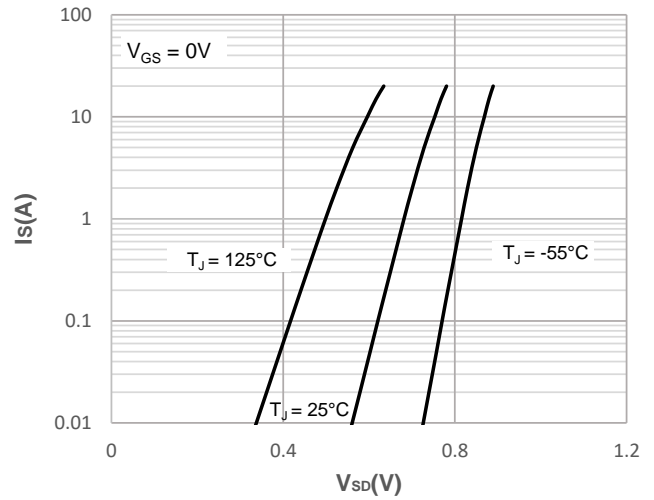


Figure 9: Gate Charge Characteristics

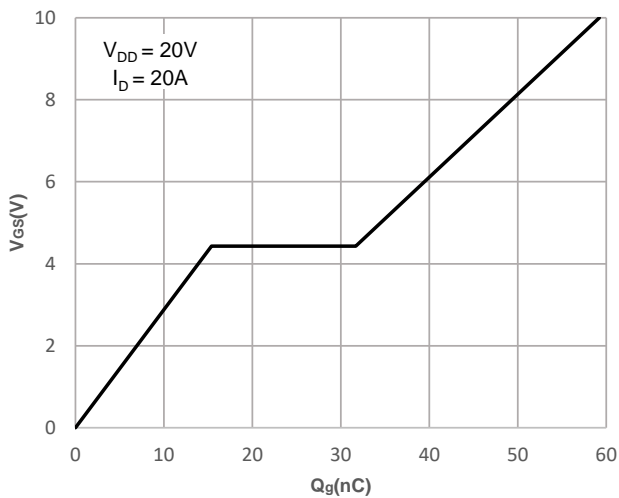
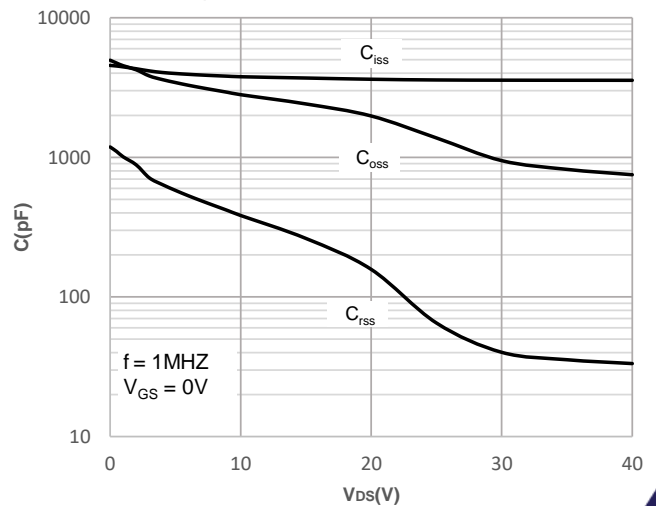


Figure 10: Capacitance Characteristics



## Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

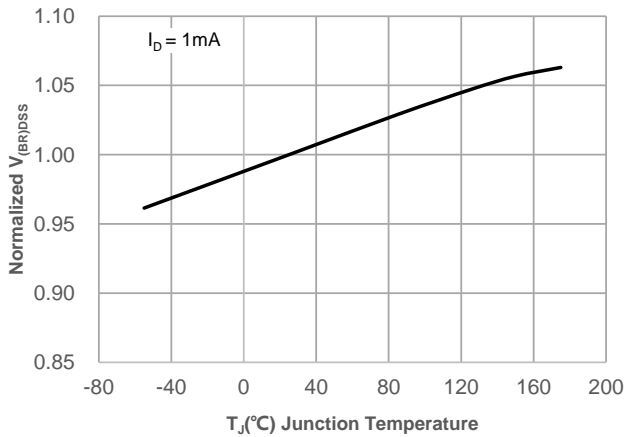


Figure 12: Normalized on Resistance vs. Junction Temperature

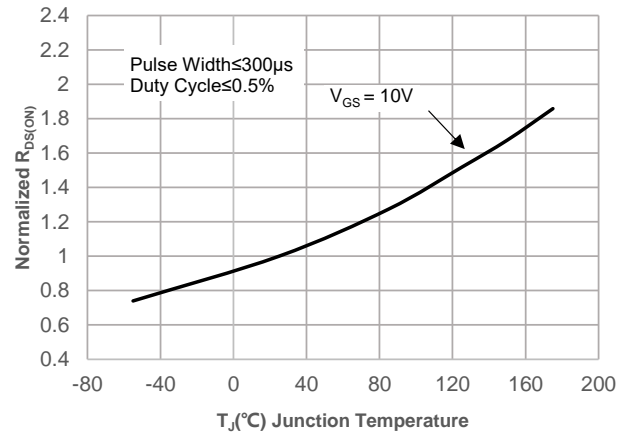


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

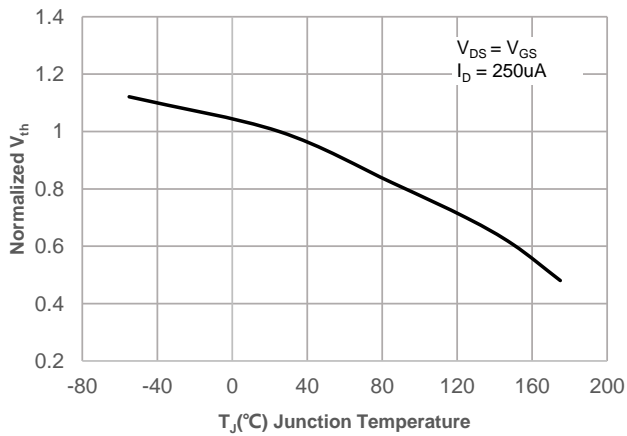


Figure 14:  $R_{DS(ON)}$  vs.  $V_{GS}$

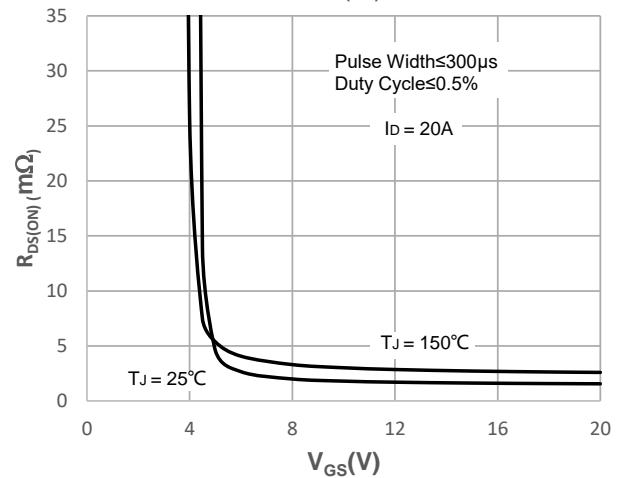
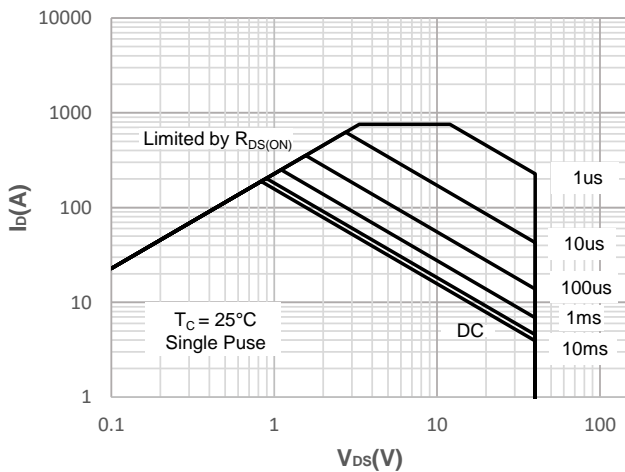


Figure 15: Maximum Safe Operating Area



## Test Circuit

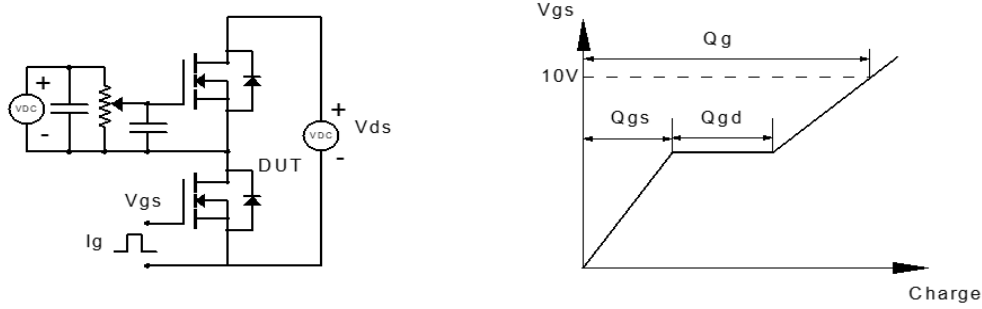


Figure 1: Gate Charge Test Circuit & Waveform

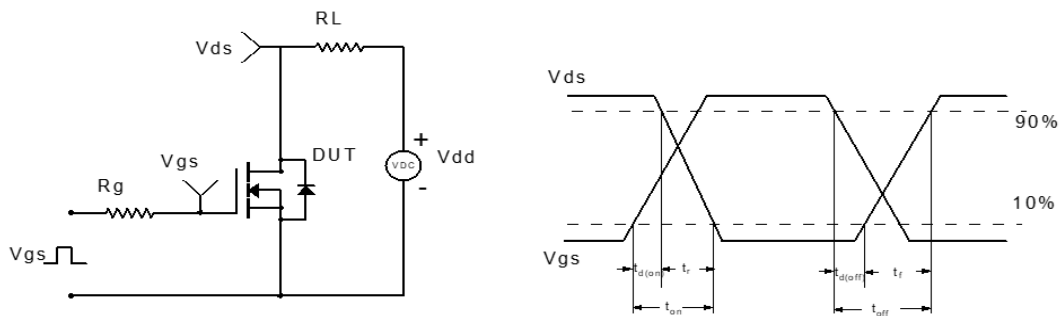


Figure 2: Resistive Switching Test Circuit & Waveform



Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

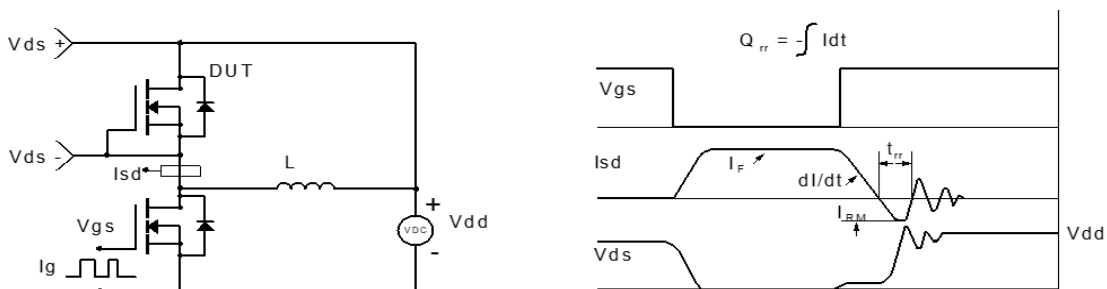


Figure 4: Diode Recovery Test Circuit & Waveform

